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MMBT2222A TRANSISTOR (NPN)

SOT-23 Plastic-Encapsulate Transistors

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客户确认：

公司签章：

部门	工程部	品保部	采购部
签名			
日期			



SOT-23 Plastic-Encapsulate Transistors

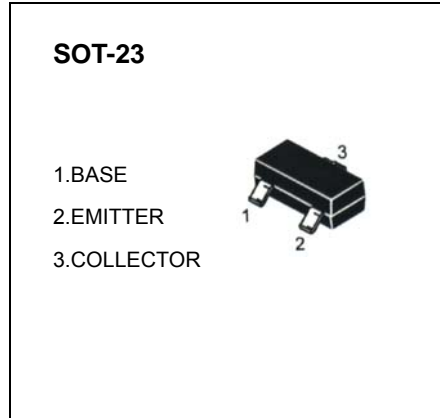
MMBT2222A TRANSISTOR (NPN)

FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMBT2907A)

MARKING: 1P

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)



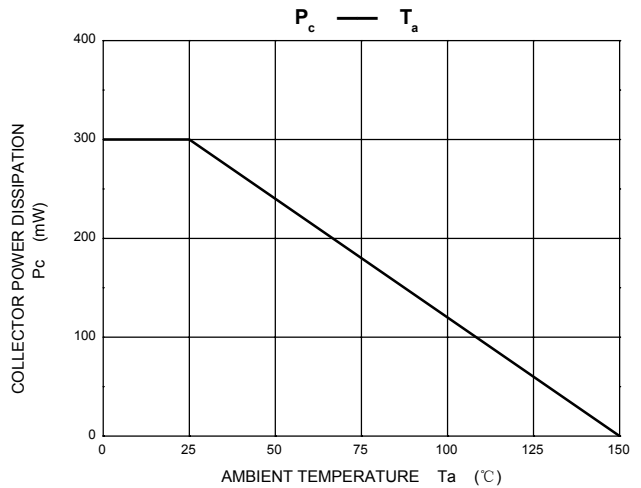
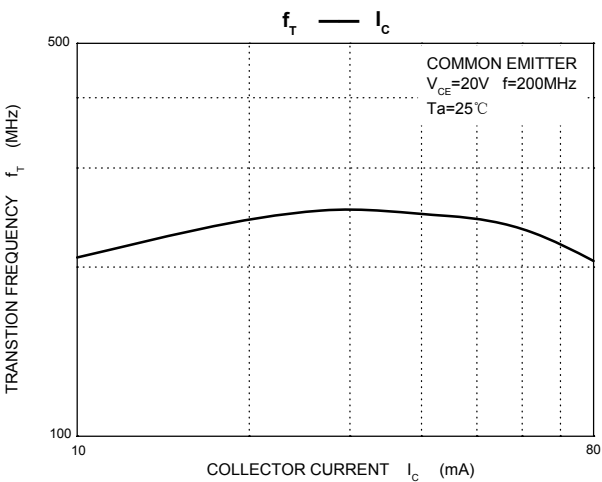
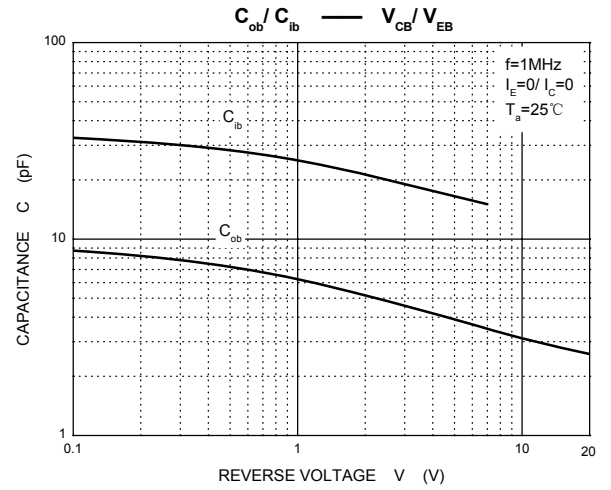
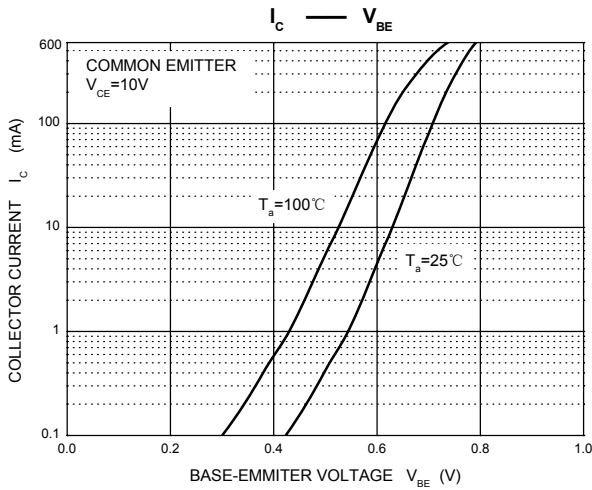
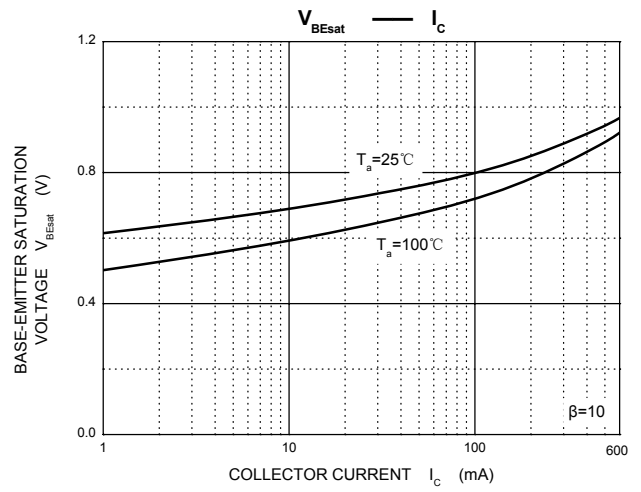
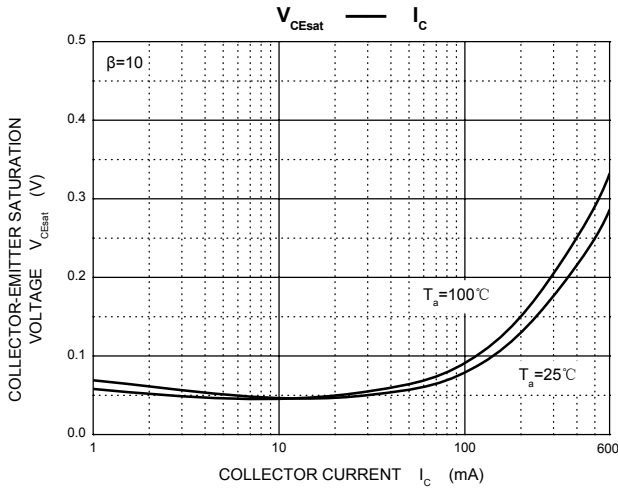
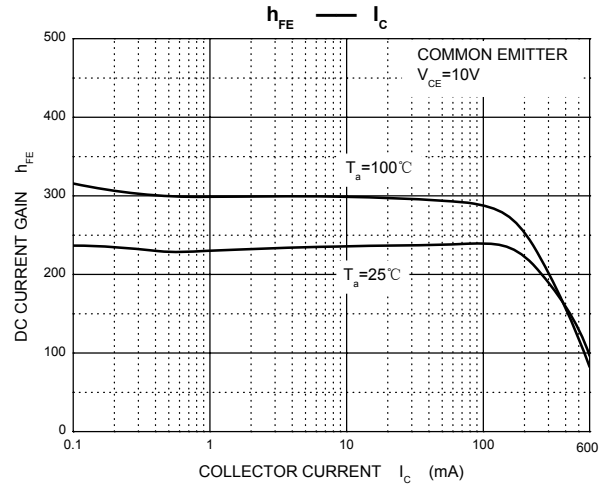
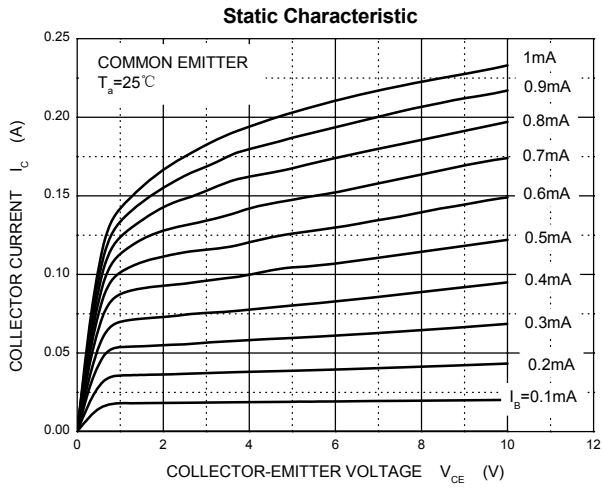
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	75	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Dissipation	250	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	500	$^{\circ}\text{C}/\text{W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55to+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

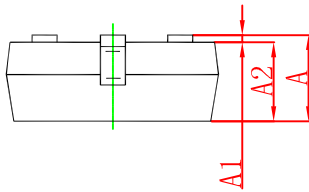
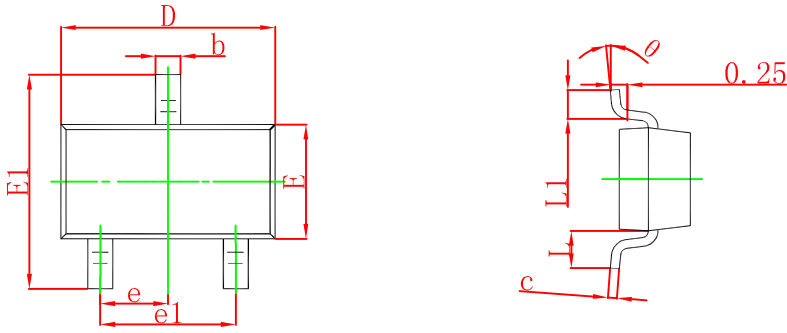
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	75			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=10\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.01	μA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$			0.01	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=3\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100		300	
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	40			
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	42			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=150\text{mA}, I_B=15\text{mA}$			1 0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=500\text{mA}, I_B=50\text{mA}$ $I_C=150\text{mA}, I_B=15\text{mA}$			2.0 1.2	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=20\text{mA}, f=100\text{MHz}$	300			MHz
Delay time	t_d	$V_{CC}=30\text{V}, V_{BE(off)}=-0.5\text{V}$			10	nS
Rise time	t_r	$I_C=150\text{mA}, I_{B1}=15\text{mA}$			25	nS
Storage time	t_s	$V_{CC}=30\text{V}, I_C=150\text{mA}$			225	nS
Fall time	t_f	$I_{B1}=-I_{B2}=15\text{mA}$			60	nS

*pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycles $\leq 2.0\%$.

Typical Characteristics

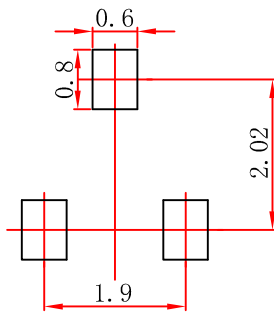


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.